

## 1710~1785 MHz Single-Bias GaAs Low Noise Amplifier

### FEATURES

- 50 ohm matched for 1710~1785 MHz
- 24 dBm Typical P1dB
- 16 dB Typical Linear Power Gain
- 36 dBm Typical IP3
- 1.1 dB Typical noise figure
- Nominal PAE of 26%
- Breakdown Voltage:  $BV_{DGO} \geq 15V$
- 6.0 Volt single bias
- Suitable for High Reliability Application

### PHOTO ENLARGEMENT



### DESCRIPTION

The TC3843A is a single-bias with 50 ohm matched GaAs FET. It is designed for low cost, high volume, applied for 1710~1785 MHz low noise amplifiers. It provides noise figure of 1.1 dB, gain of 16 dB and P1dB of 24 dBm, typically. The single positive drain bias is 6 V and the typical drain-source current is 160 mA. The device is packaged in a copper based ceramic 10-pin SMT packages. The copper based carrier of the package allows direct soldering of the device to the PCB.

### ELECTRICAL SPECIFICATIONS ( $T_A=25^\circ C$ )

Symbol	CONDITIONS	MIN	TYP	MAX	UNIT
FREQ	Frequency Range	1710		1785	MHz
$P_{1dB}$	Output Power at 1dB Gain Compression Point, $V_{DS} = 6 V$	22	24		dBm
$G_L$	Linear Power Gain, $V_{DS} = 6 V$	14	16		dB
IP3	Intercept Point of the 3 <sup>rd</sup> -order Intermodulation, $V_{DS} = 6 V$ , $*P_{SCL} = 14 dBm$	33	36		dBm
NF	Noise Figure, $V_{DS} = 6 V$		1.1	1.5	dB
PAE	Power Added Efficiency at 1dB Compression Power		26		%
$I_{DS}$	Drain-Source Current at $V_{DS} = 6 V$		160	220	mA
$BV_{DGO}$	Drain-Gate Breakdown Voltage at $I_{DGO} = 0.6 mA$	15	18		Volts

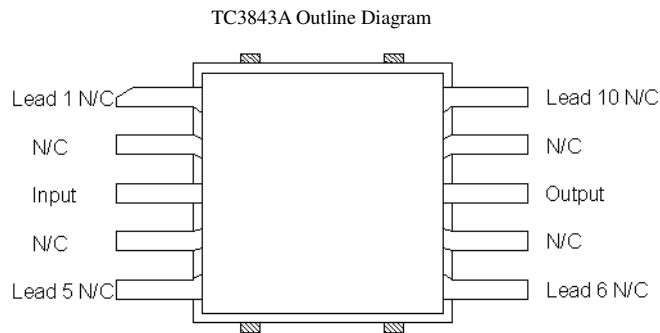
**Note:  $*P_{SCL}$ : Output Power of Single Carrier Level.**

### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ C$ ) RECOMMENDED OPERATING CONDITION

Symbol	Parameter	Rating	Symbol	Parameter	Rating
$V_{DS}$	Drain-Source Voltage	10 V	$V_{DS}$	Drain to Source Voltage	6 V
$P_{in}$	RF Input Power, CW	26 dBm			
$P_T$	Continuous Dissipation	2.0 W			
$T_{CH}$	Channel Temperature	175 °C			
$T_{STG}$	Storage Temperature	- 65 °C to +175 °C			

### HANDLING PRECAUTIONS

The user must operate in a clean, dry environment. Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. The static discharge must be less than 300V.

**CONNECTION DIAGRAM**


\* Note : Grounding is via package case

**EVALUATION BOARD**

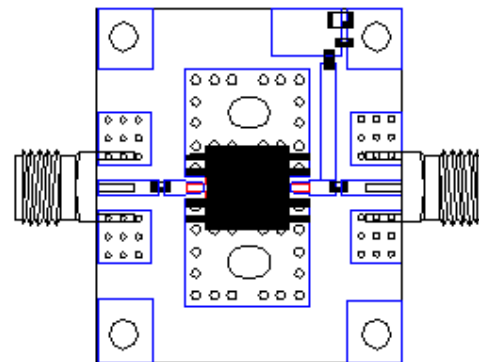
**PCB Material: FR4**

**ER = 4.6**

**Thickness = 31 mil**

\* Application Notes:

For better heat sinking and grounding, it's recommended to have via holes beneath TC3843A filled with solder and have two screws installed on required heat sink plate besides TC3843A on the PCB area.



**C1 chip capacitor : 100 pF**

**C2 chip capacitor : 100 pF**

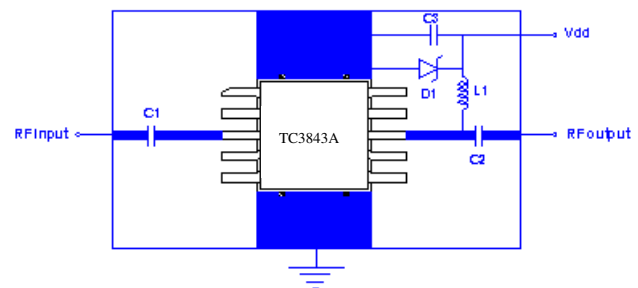
**C3 capacitor : 0.22 uF**

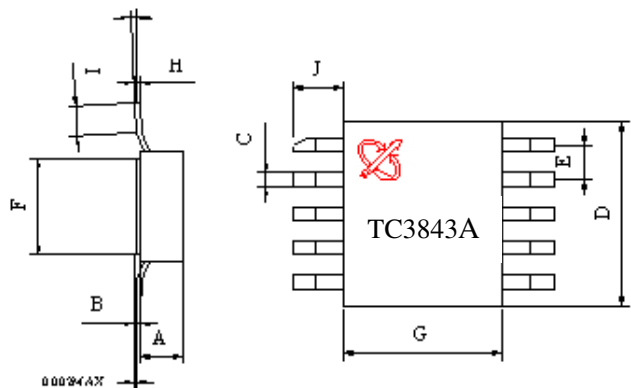
**L1 : 160 nH**

**D1 Zener Diode : 7.0 V**

**50 ohm microstrip line**

TC3843A Evaluation Circuit



**PHYSICAL DIMENSIONS** (Unit: inches)


DIMENSION	MINIMUM	NOMINAL	MAXIMUM
A	0.054	0.057	0.060
B	0.007	0.008	0.009
C	0.017	0.020	0.023
D	0.267	0.270	0.273
E	0.047	0.050	0.053
F	0.247	0.250	0.253
G	0.267	0.270	0.273
H	0.007	0.008	0.009
I	0.020		0.040
J	0.073	0.080	0.087
$\alpha$	0°		7°